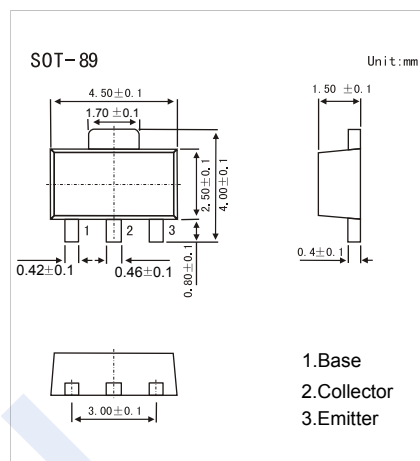


PNP Transistors

2SB1000

■ Features

- Low frequency power amplifier
- Complementary to 2SD1366

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-25	V
Collector - Emitter Voltage	V_{CE0}	-20	
Emitter - Base Voltage	V_{EB0}	-5	
Collector Current - Continuous	I_C	-1	A
Collector current -Pulse (Note.1)	I_{CP}	-1.5	
Collector Power Dissipation	P_C	1	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

Note.1: $PW \leq 10\text{ms}$, Duty cycle $\leq 20\%$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = -100 \mu\text{A}$, $I_E = 0$	-25			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = -1 \text{ mA}$, $I_B = 0$	-20			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -100 \mu\text{A}$, $I_C = 0$	-5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -20\text{V}$, $I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4\text{V}$, $I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -800 \text{ mA}$, $I_B = -80 \text{ mA}$		-0.2	-0.3	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -800 \text{ mA}$, $I_B = -80 \text{ mA}$		-0.94	-1.1	
DC current gain	h_{FE}	$V_{CE} = -2\text{V}$, $I_C = -500 \text{ mA}$	85		240	
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$		38		pF
Transition frequency	f_T	$V_{CE} = -2\text{V}$, $I_C = -500 \text{ mA}$		200		MHz

■ Classification of h_{FE}

Type	2SB1000-H	2SB1000-J
Range	85-170	120-240
Marking	AH	AJ

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2SB1000

■ Typical Characteristics

MAXIMUM COLLECTOR DISSIPATION
CURVE

